CLAIM AMENDMENTS

1. (Currently Amended) A semiconductor device having a pad region and a circuit region, comprising:

a low-k dielectric film ~~formed~~ on a pad region and a circuit region of a substrate, the low-k dielectric film having dielectric constant of no more than 3 ~~or less~~;

an insulating film ~~formed in~~ on the low-k dielectric film of the pad region, the insulating film having higher strength than the low-k dielectric film;

multi-layer wirings ~~formed in~~ on the insulating film of the pad region and ~~in~~ on the low-k dielectric film of the circuit region; and

a bonding pad ~~formed~~ on ~~a highest~~ an outermost wiring of the multi-layer wirings of the pad region.

2. (Currently Amended) The semiconductor device according to claim 1, wherein sidewalls of the wiring ~~formed~~ in the pad region are surrounded by the ~~insulting~~ insulating film.

3. (Currently Amended) The semiconductor device according to claim 1, wherein the low-k dielectric film is an insulating film containing silicon, carbon, oxygen, and hydrogen ~~or a polymer film containing hydrogen and carbon~~.

4. (Currently Amended) A semiconductor device having a pad region and a circuit region, comprising:

multi-layer low-k dielectric films ~~formed~~ on a pad region and a circuit region of a substrate, each of the multi-layer low-k dielectric films having a dielectric constant of no more than 3 ~~or less~~;

insulating films ~~formed in~~ on each of the multi-layer low-k dielectric films of the pad region, each of the insulating films having higher strength than the low-k dielectric film;

wirings ~~formed in~~ on each of the insulating films of the pad region and ~~in~~ on each of the low-k dielectric films of the circuit region; and

a bonding pad ~~formed~~ on ~~a highest~~ an outermost wiring of the wirings of the pad region.

5. (Currently Amended) The semiconductor device according to claim 4, wherein sidewalls of the wirings ~~formed~~ in the pad region are surrounded by the ~~insulting~~ insulating films.

6. (Currently Amended) A method for manufacturing a semiconductor device having a pad region and a circuit region, comprising:

forming a low-k dielectric film on an entire surface of a substrate, the low-k dielectric film having dielectric constant of no more than 3 ~~or less~~;

forming an opening in the low-k dielectric film of the pad region;

forming a first insulating film having higher strength than the low-k dielectric film in the opening; and

forming wirings ~~in~~ on the first insulating film of the pad region and ~~in~~ on the low-k dielectric film of the circuit region using a damascene process.

7. (Currently Amended) The manufacturing method according to claim 6, wherein the forming an opening includes:

forming a second insulating film on the low-k dielectric film;

forming a resist pattern on the second insulating film; and

patterning the second insulating film and the low-k dielectric film using the resist pattern as mask, ~~and~~ wherein the first insulating film ~~is formed so that~~ has a surface ~~of the first insulating film is higher~~ further from the substrate than a surface of the low-k dielectric film and is ~~lower~~ closer to the substrate than a surface of the resist pattern.

8. (Currently Amended) The manufacturing method according to claim 6, wherein, in ~~the~~ forming the a first insulating film, forming a silicon oxide film ~~is formed using a~~ by liquid-phase deposition ~~method~~.

9. (Currently Amended) The manufacturing method according to claim 6, including forming the multi-layer wirings ~~are formed~~ by ~~repeating the~~ repeatedly forming a low-k dielectric film, forming an opening, forming a first insulating film, and forming wirings, and

~~wherein~~ forming a bonding pad ~~is formed~~ on a ~~highest~~ wiring of the multi-layer wirings of the pad region most distant from the substrate.

10. (New) The semiconductor device according to claim 1, wherein the low-k dielectric film is a polymer film containing hydrogen and carbon.